

IRFS3206TRRPBF

Data Sheet

60V Single N-Channel HEXFET Power MOSFET in a D2-Pak package; Similar to IRFS3206PBF with Tape and Reel Right packaging.

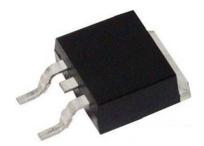
Manufacturers <u>Infineon Technologies Corporation</u>

Package/Case D2PAK

Product Type Transistors

RoHS Green

Lifecycle



Images are for reference only

Please submit RFQ for IRFS3206TRRPBF or Email to us: sales@ovaga.com We will contact you in 12 hours.

RFO

General Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

Advanced Process Technology

Ultra Low On-Resistance

Enhanced dV/dT and dI/dT capability

175°C Operating Temperature

Fast Switching

Repetitive Avalanche Allowed up to Tjmax

Lead-Free, RoHS Compliant

Automotive Qualified

Features

Advanced Process Technology

Ultra Low On-Resistance

Enhanced dV/dT and dI/dT capability

175°C Operating Temperature

Fast Switching

Repetitive Avalanche Allowed up to Tjmax

Lead-Free, RoHS Compliant

Automotive Qualified

Related Products



IRLTS6342TRPBF

Infineon Technologies Corporation TSOP-6



IRF9310PBF

Infineon Technologies Corporation SOIC-8



IRF9358TRPBF

Infineon Technologies Corporation SOP-8



IRFB3307ZPBF

Infineon Technologies Corporation TO-220AB



IRLHS6376TRPBF

Infineon Technologies Corporation PQFN2x2DD



IRFH9310TRPBF

Infineon Technologies Corporation PQFN-8



IRFB7430PBF

Infineon Technologies Corporation TO-220



IRF7351TRPBF

Infineon Technologies Corporation SOIC-8